



# N-Channel 75-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>(BR)DSS</sub> (V)	$r_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)	
75	0.0062 at V <sub>GS</sub> = 10 V	90 <sup>d</sup>	75	

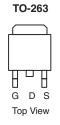
## **FEATURES**

- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R<sub>q</sub> and UIS Tested

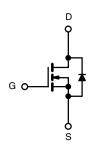


#### **APPLICATIONS**

- Power Supply
  - Secondary Synchronous Rectification
- Industrial



Ordering Information: SUM90N08-6m2P-E3 (Lead (Pb)-free)



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	T <sub>C</sub> = 25 °C, unless oth	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	75	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current (T <sub>.1</sub> = 175 °C)	T <sub>C</sub> = 25 °C	I-	90 <sup>d</sup>		
Continuous Diam Current (1, = 175 C)	T <sub>C</sub> = 70 °C		90 <sup>d</sup>		
Pulsed Drain Current		I <sub>DM</sub>	240	- A	
Avalanche Current	I <sub>AS</sub>	50			
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
	T <sub>C</sub> = 25 °C	В	272 <sup>b</sup>	14/	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C <sup>c</sup>	$ P_D$ $-$	3.75	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.55			

## Notes:

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.

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<b>SPECIFICATIONS</b> $T_J = 25$ °	C, unless of	therwise noted				
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	75			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4.5	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
		$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50	
		$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 ^{\circ}\text{C}$			250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	70			Α
Drain-Source On-State Resistance <sup>a</sup>	r	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.0051	0.0062	Ω
	<sup>r</sup> DS(on)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.0082	0.0105	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		50		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			4620		pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$		517		
Reverse Transfer Capacitance	C <sub>rss</sub>			247		
Total Gate Charge <sup>c</sup>	$Q_g$	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A		75	115	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			25.5		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			20		
Gate Resistance	$R_g$	f = 1 MHz		1.2	2.4	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			16	30	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 30 V, $R_L$ = 0.6 $\Omega$		11	20	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		24	40	
Fall Time <sup>c</sup>	t <sub>f</sub>			10	20	
Source-Drain Diode Ratings and Ch	aracteristics 7	<sub>C</sub> = 25 °C <sup>b</sup>				
Continuous Current	Is				85	Α
Pulsed Current	I <sub>SM</sub>				240	
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		0.83	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 75 A, di/dt = 100 A/μs		60	100	ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>			3.3	5	Α
Reverse Recovery Charge	Q <sub>rr</sub>			100	150	nC

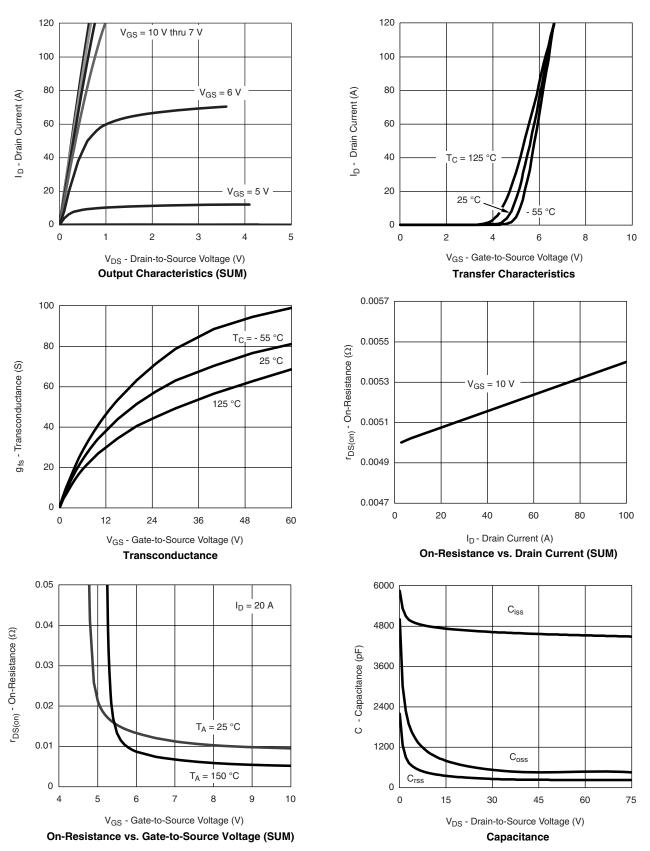
## Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

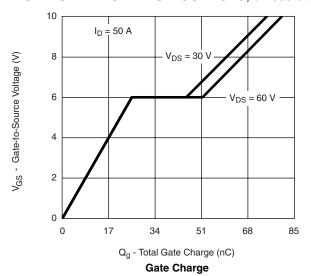


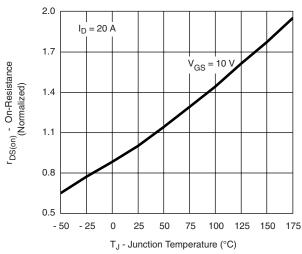
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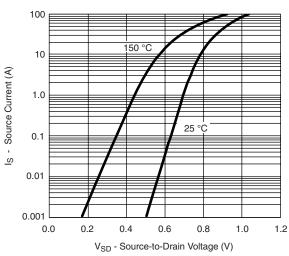
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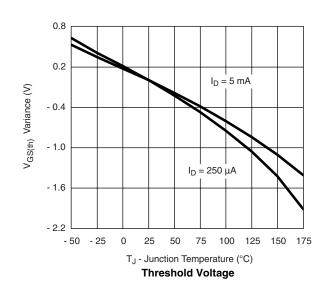
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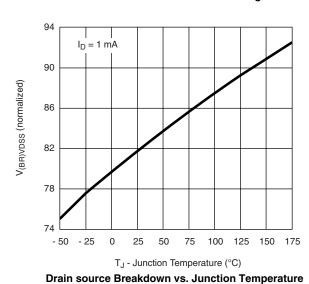


On-Resistance vs. Junction Temperature





Source-Drain Diode Forward Voltage



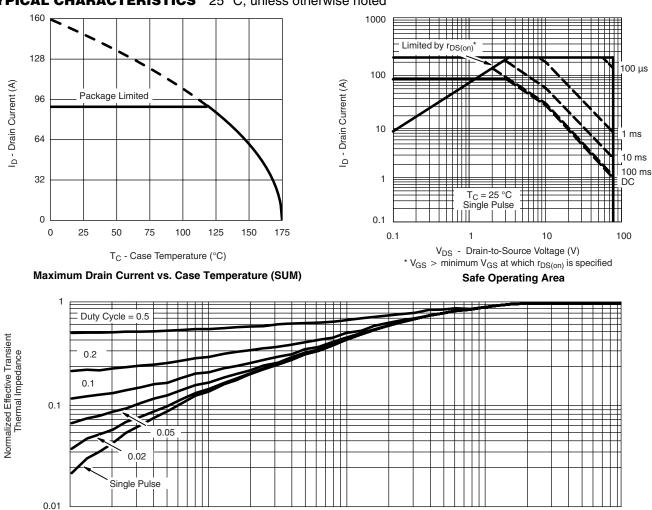
100 150 °C 25 °C 10 0.00001 0.001 0.01 0.1 1.0 T<sub>AV</sub> (s)

Single Pulse Avalanche Current Capability vs. Time

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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

10-3



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Case

10-2

10-1

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